3rd JST/CREST/2D Workshop in Singapore

Date: Friday 15 March 2019 Time: 16:00 to 19:00 hrs Venue: Melati Junior Ballroom, Marina Bay Sands Convention Centre, Singapore Registration fee: Free for 2019 EDTM registered participants **Technical Programme:** 16:00 Greeting, Atsushi Kurobe, Toshiba 16:05 Keynote, Kaustav Banerjee, UCSB, "2D Materials for Next-Generation LSI and IoT Devices" 16:35 Invited, Kah-Wee Ang, NUS "Rediscovering black phosphorus layered material for electronic and optoelectronic device applications" 17:05 Manabu Ohtomo, Fujitsu, "Bottom-up synthesis of edge-functionalized graphene nanoribbons for heterojunction devices" 17:25 Coffee Beak 17:35 Yasumitsu Miyata, Tokyo Metropolitan Univ., "Semiconductor heterojunctions based on 2D materials" 17:55 Tomoki Machida, Institute of Industrial Science, University of Tokyo "Robotic assembly and mid-infrared photoresponse of van der Waals junctions of graphene and 2D materials" Atsushi Ogura / Yusuke Hibino, Meiji Univ., 18:15 "Fabrication of various TMD materials with MOCVD and sputtering deposition" 19:35 Hitoshi Wakabayashi, Tokyo Tech, "2D FET and Materials using Sputtering" 18:55 Closing remarks, Hitoshi Wakabayashi, Tokyo Tech

This workshop is sponsored by JST and technically supported by 2019 EDTM.

19:00

Adjourn